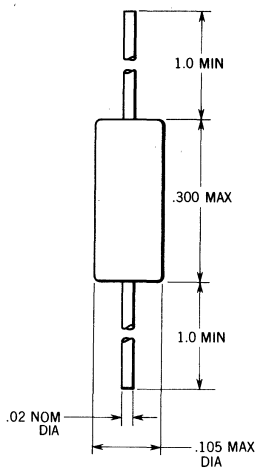
1N458
LOW LEAKAGE PLANAR* DIODE

MAXIMUM RATINGS (25°C) [Note 1]

WIV	Working Inverse Voltage	125 V
I_o	Average rectified current	55 mA
i_F	Forward current steady state d.c.	115 mA
I_f	Recurrent peak forward current	175 mA
i_f (surge)	Peak forward surge current pulse width of 1 second	500 mA
i_f (surge)	Peak forward surge current pulse width of 1 μs	2A
P	Power dissipation	400 mW
T_A	Operating temperature	−65°C to +150°C
T_{stg}	Storage temperature, ambient	−65°C to +175°C

PHYSICAL DIMENSIONS
(All dimensions in inches)



ELECTRICAL SPECIFICATIONS (25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
V_F	Forward Voltage			1.0	Volts	$I_F = 7.0$ mA
I_R	Reverse Current			25	nA	$V_R = -125$ V
I_R	Reverse Current (150°C)			5.0	μA	$V_R = -125$ V
BV	Breakdown Voltage	150			Volts	$I_R = 100$ μA
C_o	Capacitance (f = 1 MHz) [Note 2]			6.0	pF	$V_R = 0$ V

* Planar is a patented Fairchild process.

NOTES:
(1) The maximum ratings are limiting values above which life or satisfactory performance may be impaired.
(2) Capacitance as measured on Boonton Electronic Corporation Model No. 75A-S8 Capacitance Bridge or equivalent.

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